Efficient Routing for CGRAs using Multi-Pole NEM Relays

ASP-DAC 2022: SESSION 14

EMERGING DEVICES, TECHNOLOGIES, AND APPLICATIONS

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*Equal contribution

Designing an application today

CPU, GPU, FPGA, and ASICs Tradeoffs



Where does reconfigurability overhead come from?

Reconfigurable routing

- Huge multiplexer cost
- FPGA compared to ASIC:
 - Area 20-35x
 - Power 5-12x
 - Delay 3-4x

Source: Kuon, Ian, and Jonathan Rose. "Measuring the gap between FPGAs and ASICs." *IEEE Transactions on computer-aided design of integrated circuits and systems* 26, no. 2 (2007): 203-215.

Configuration memory

- Startup time: SRAM-based FPGAs take milliseconds to seconds to copy configuration data from off-chip to on-chip
- SRAM takes silicon area and consumes static power
- Increases startup power/area/delay for intermittent applications

Both routing & config memory are control plane components

Coarse Grained Reconfigurable Array (CGRA)



Processing Element (PE) Memory (MEM) Switch box (SB) Connection box (CB)



Connection Box (CB)

Each PE needs two 10:1 CB muxes and control registers for them

10 horizontal 16-bit tracks 5 driven left, 5 driven right



10 vertical 16-bit tracks 5 driven up, 5 driven down

> There are similar 1-bit CBs for feeding 1-bit inputs from 10 horizontal and vertical 1-bit tracks

Coarse Grained Reconfigurable Array (CGRA)





3D integration for CGRA control plane

- Overhead comes from control plane components
- 3D advantages: less silicon area, shorter wire lengths, heterogeneous
- Control plane components are less sensitive to write speed
- Control/data plane: different physical planes of integrated 3D design



Emerging nanotechnologies for reconfigurability

CGRAs:

- Reconfigurable architecture with multi-bit datapaths and wide ALUs **NEM relays:**
- Nano-scale mechanical switches monolithically integrated in 3D
- Reduce area/power/delay overhead from reconfigurable interconnects



Nanoelectromechanical (NEM) Relays

- Nanoscale mechanical relays
- Electrically actuated by Coulomb force between body and gate
- Can have four terminals, like MOSFET (G, D, S, B)
- Current flow between source and drain is controlled by potential across body and gate
- Behaves like pass gate
 - No threshold voltage drop
- Only 5-7 mask layers are required @ below 400°C





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NEM Relay I-V Characteristic

- Zero OFF-state/subthreshold leakage
- Abrupt ON/OFF behavior
- Low ON resistance
- Lower pull-out voltage due to mechanical instability & stiction
- Hysteresis
 - State memory
 - Need to ensure you have high enough voltage swing at gate to overcome hysteresis



Multi-Pole NEM Relay

- Multiple channels connecting different source-drain pairs
- Share same gate and body

Insight: multi-pole NEM relay can route *multi-bit digital signals*



Contributions of Our Work

1) Improved multi-pole NEM relay design



2) Methodology for multi-pole contact placement



 CMOS-NEMS integration methodology and demo of hybrid CMOS-NEMS CGRA PE tile



Multi-Pole NEM Relay Design

Folded beams for space saving without increasing spring constant



Multi-Pole NEM Relay Design

Anchor sharing for reducing area overhead over relay mosaic



Multi-Pole NEM Relay Design

Result: area utilization is improved over prior design



Footprint comparison

Multi-Pole NEM Relay Contact Placement

- Multi-pole relays: where to place the contacts?
 - Contacts need to touch down simultaneously
 - If misplaced, huge increase in contact resistance for some contacts
- **Example:** circular placement has huge variation in contact resistance across contacts
- How do we reduce variation?



Multi-Pole NEM Relay Contact Placement

Simulated pull-in process



Multi-Pole NEM Relay Contact Placement

- Insight: contacts need to be placed on roughly the same displacement contour
- Iterative Contact Placement (ICP)



• **Step 1:** Initialize contact placement (ex: circular placement)



• **Step 2:** Perform finite element analysis to determine displacement contour



• **Step 3:** Find contact forces and resistances at operating voltage. Check if variation is below target value



• **Step 4:** Find displacement contour at operating voltage



• **Step 5:** Pick points along displacement contour to place contacts in next iteration, and go back to step 2



Converges to very low contact resistance variation in just 3 iterations



Converges to very low contact resistance variation in just 3 iterations



Integration Methodology: Multiplexers

- How to compose relays into efficient multiplexers?
- Strategy: One-Hot Multiplexing
- Each relay takes S₀-S_{N-1} (one-hot)
- Each relay takes I₀-I_{N-1} (8 bits wide each)
- When S_i is on, I_i[7:0] is electrically connected to Z[7:0]





Integration Methodology: Design Flow

Hybrid CMOS-NEMS Multiplexer



Hybrid CMOS-NEMS CGRA PE Tile



Integration Methodology: Design Flow Challenges

Challenges:

- Power grid for NEM relay body bias should not disrupt anything
- Layout and power grid must be designed concurrently to ensure compatibility (DRC)



- CMOS cells need to be placed below NEMS layer
 - Treat NEMS as cover cells
 - Custom legalization script
 - Snap to grid
 - Auto-fix overlapping cells



Integration Methodology: Design Flow Challenges

Challenges:

- Power/delay estimation
 - NEM relays need to be treated as pass gates
 - Need to propagate parasitic capacitances back to driving cells
 - Essentially introduce pass gate logic into power/delay estimation flows
 - Developed scripts to automate integration of pass gate logic



Results: Hybrid CMOS-NEMS CGRA PE Tile

- Constrained for iso-delay: 5 ns
- **Area Benefit:** 19.2%
- **FOM:** Area FOM = $\frac{CMOS \text{ Design Stdcell Area} NEMS \text{ Design Stdcell Area}}{SB/CB \text{ Mux Area}} = 73.3\%$
- Image Processing Applications Tested (for Power):
 - 3x3 convolution
 - Cascaded convolution
 - Harris corner detector
- Average Power Benefit across Applications: 9.7%

Results: Hybrid CMOS-NEMS CGRA PE Tile Area



Most of the area reduction is in the switch box; a little in CB too Stanford University

Results: Hybrid CMOS-NEMS CGRA PE Tile Power

Tile consumed by all PE tiles for application



Power benefit is similar across applications Switchboxes dominate the PE tile power; CBs are almost zero

Results: Hybrid CMOS-NEMS CGRA PE Tile

Summary across applications



*Power is per-tile

Conclusion

Contributions:

- Improved multi-pole NEM relay design
- 2. Solving multi-pole contact placement
- 3. CMOS-NEMS integration methodology & demo of hybrid CMOS-NEMS CGRA PE tile

Results on PE tile:

- Constrained for iso-delay
- 19.2% area improvement
- 9.7% power improvement



Thank you!

$\mathsf{QUESTIONS?}$

